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2SA1052

Silicon PNP Epitaxial



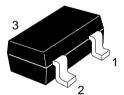
ADE-208-1006A (Z) 2nd. Edition Mar. 2001

Application

Low frequency amplifier

Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector

2SA1052

Absolute Maximum Ratings (Ta = 25°C)

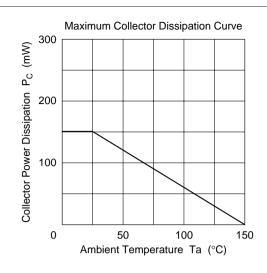
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-30	V
Collector to emitter voltage	V_{CEO}	-30	V
Emitter to base voltage	V_{EBO}	- 5	V
Collector current	I _c	-100	mA
Emitter current	I _E	100	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

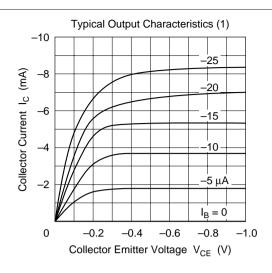
Electrical Characteristics ($Ta = 25^{\circ}C$)

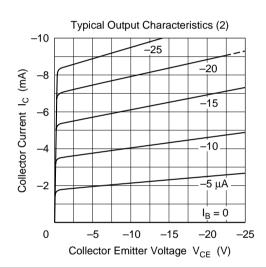
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-30	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-30	_	_	V	$I_{c} = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	_	_	V	$I_{E} = -10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	-0.5	μΑ	$V_{CB} = -20 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	-0.5	μΑ	$V_{EB} = -2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	100	_	500		$V_{CE} = -12 \text{ V}, I_{C} = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	-0.2	V	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -1 \text{ mA}$
Base to emitter voltage	V_{BE}	_	_	-0.75	V	$V_{CE} = -12 \text{ V}, I_{C} = -2 \text{ mA}$

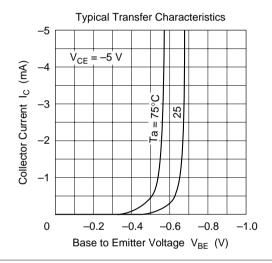
Note: 1. The 2SA1052 is grouped by h_{FE} as follows.

Grade	В	С	D
Mark	MB	MC	MD
h _{FE}	100 to 200	160 to 320	250 to 500

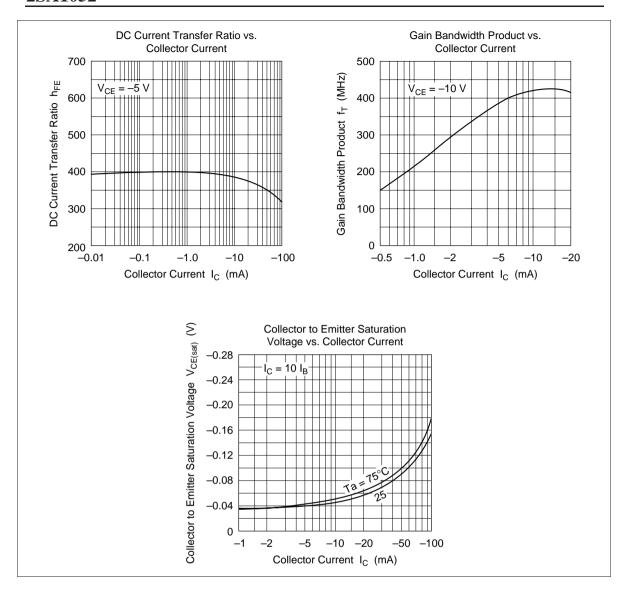




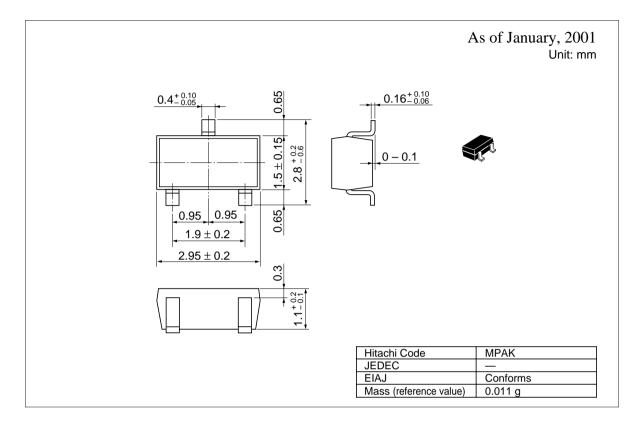




2SA1052



Package Dimensions



5

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